

• General Description

The AGM30P25M combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

• Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- 100% Avalanche tested
- 100% DVDS tested

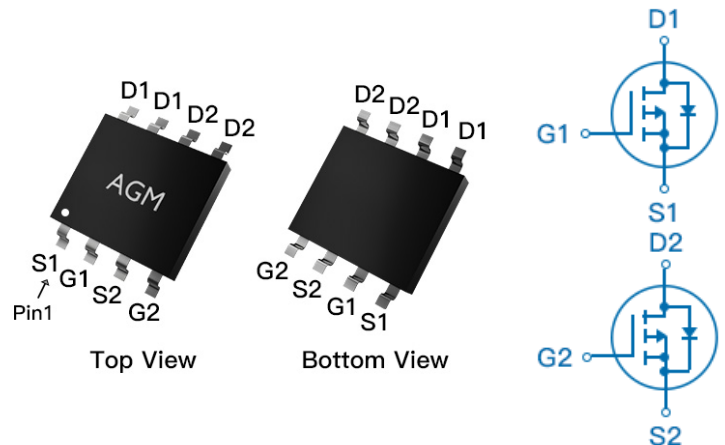
• Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
-30V	22mΩ	-8A

SOP8 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM30P25M	AGM30P25M	SOP8	330mm	12mm	3000

Table 1. Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	-30	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25°C) (Note 1)	-8	A
	Drain Current-Continuous(Tc=100°C)	-4.8	A
IDM (pluse)	Drain Current-Pulsed (Note 2)	-32	A
PD	Maximum Power Dissipation(Tc=25°C)	2.5	w
	Maximum Power Dissipation(Tc=100°C)	1.0	w
EAS	Avalanche energy (Note 3)	64	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) ¹	---	50	°C/W

Table 2. P-Channel Electrical Characteristics (TJ=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=-250μA	-30	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=-30V,VGS=0V	--	--	-1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=-250μA	-1.2	-1.5	-2.2	V
gFS	Forward Transconductance	VDS=-5V,ID=-4A	--	6	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=-10V, ID=-5A	--	22	28	mΩ
		VGS=-4.5V, ID=-4A	--	31.5	40	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=-15V,VGS=0V, F=1MHZ	--	652	--	pF
Coss	Output Capacitance		--	95	--	pF
Crss	Reverse Transfer Capacitance		--	85.7	--	pF
Switching Times						
td(on)	Turn-on Delay Time	VGS=-10V,VDS=-15V, ID=-4A,RGEN=3Ω, RL=3.6Ω	--	8.0	--	nS
tr	Turn-on Rise Time		--	4.0	--	nS
td(off)	Turn-Off Delay Time		--	26	--	nS
tf	Turn-Off Fall Time		--	12.5	--	nS
Qg	Total Gate Charge	VGS=-10V, VDS=-15V, ID=-1A	--	14	--	nC
Qgs	Gate-Source Charge		--	1.3	--	nC
Qgd	Gate-Drain Charge		--	3.0	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	-8	A
VSD	Forward on Voltage	VGS=0V,IS=-5A	--	--	-1.2	V
trr	Reverse Recovery Time	IF=-5A , dl/dt=100A/μs ,	--	--	--	ns
Qrr	Reverse Recovery Charge	TJ=25℃	--	--	--	nc

Notes 1.The maximum current rating is package limited.

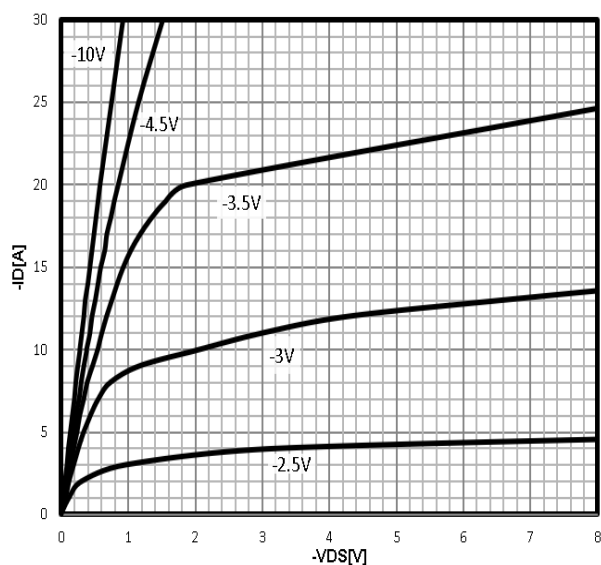
Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: TJ=25°C, VDD=-15V, Vgs=-10V, ID=-16A, L=0.5mH, RG=25ohm

Characteristics Curve:

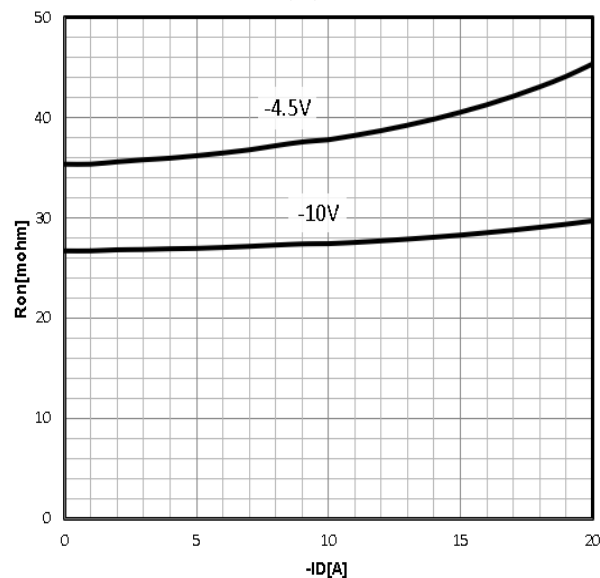
Typ. output characteristics

$$I_D = f(V_{DS})$$



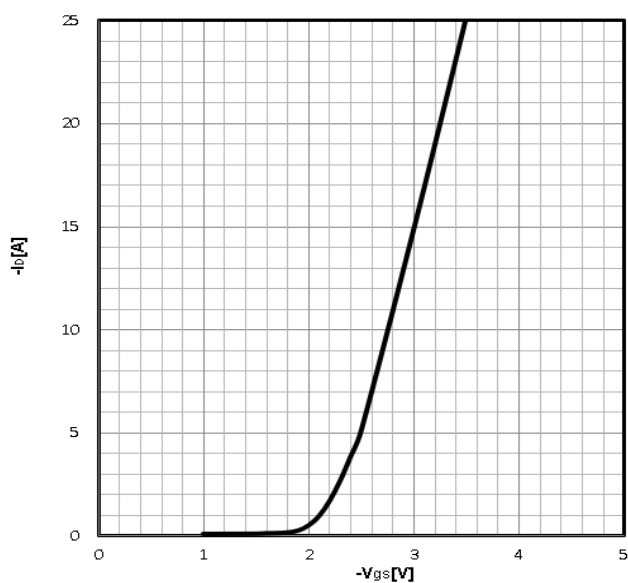
Typ. drain-source on resistance

$$R_{DS(on)} = f(I_D)$$



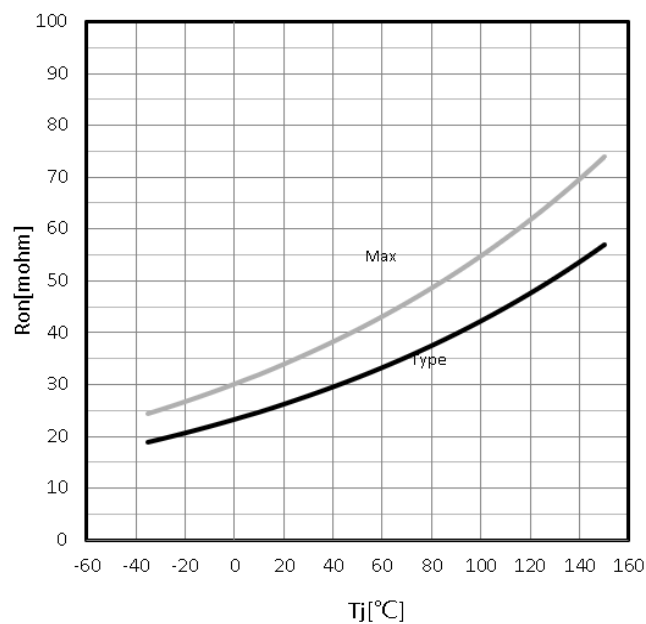
Typ. transfer characteristics

$$I_D = f(V_{GS})$$

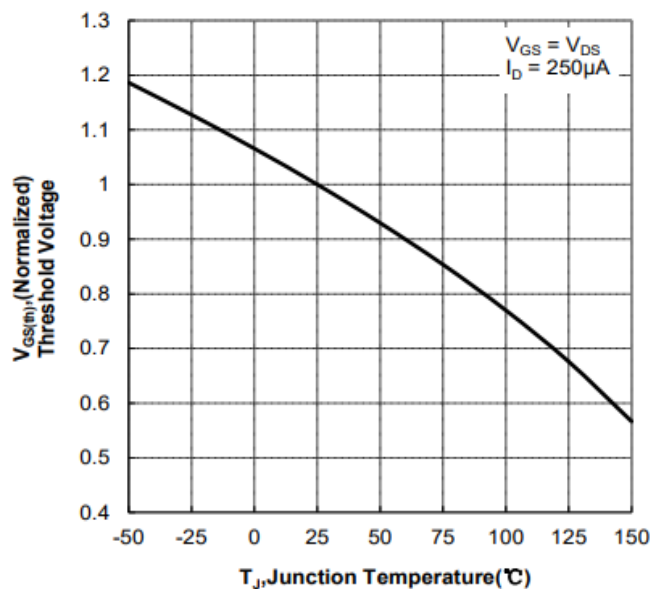


Drain-source on-state resistance

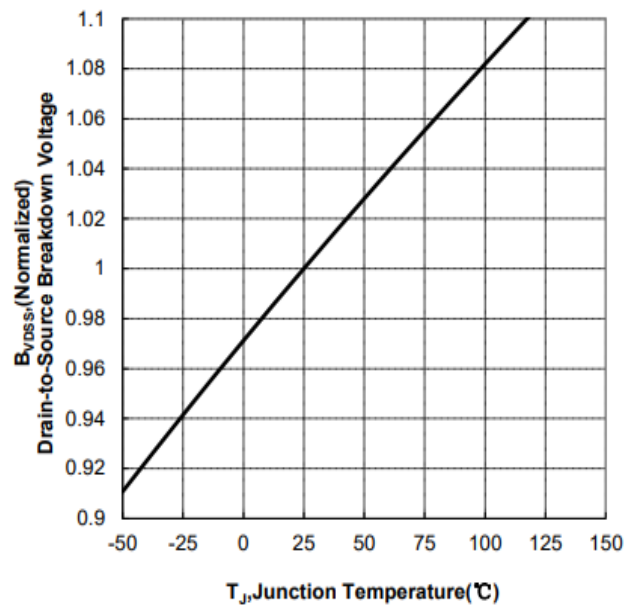
$$R_{DS(on)} = f(T_j); I_D = -5A; V_{GS} = -10V$$



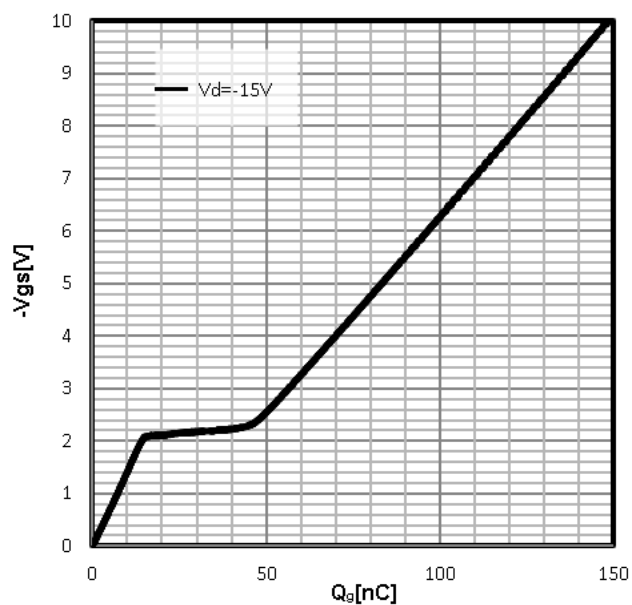
Gate Threshold Voltage
 $-V_{TH}=f(T_j); I_D=-250\mu A$



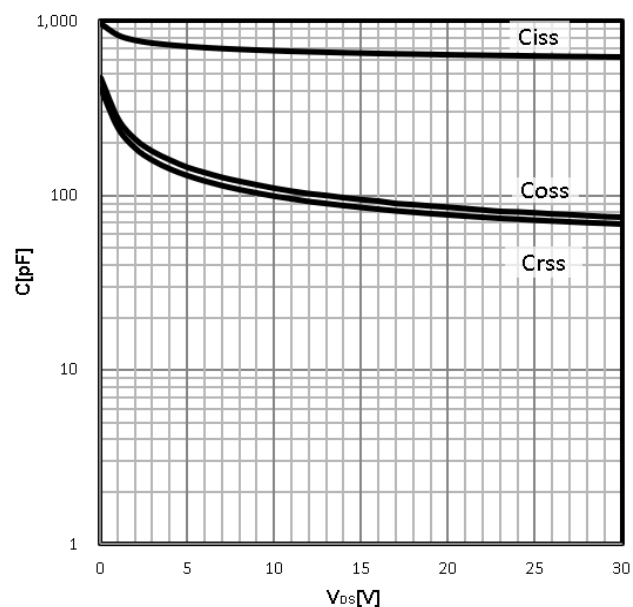
Drain-source breakdown voltage
 $V_{BR(DSS)}=f(T_j); I_D=-250\mu A$



Typ. gate charge
 $V_{GS}=f(Q_{gate}); I_D=-1A$

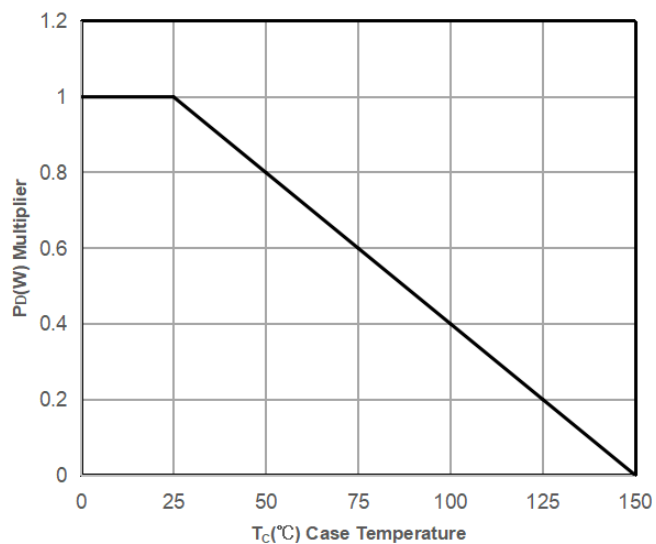


Typ. capacitances
 $C=f(V_{DS}); V_{GS}=0V; f=1MHz$



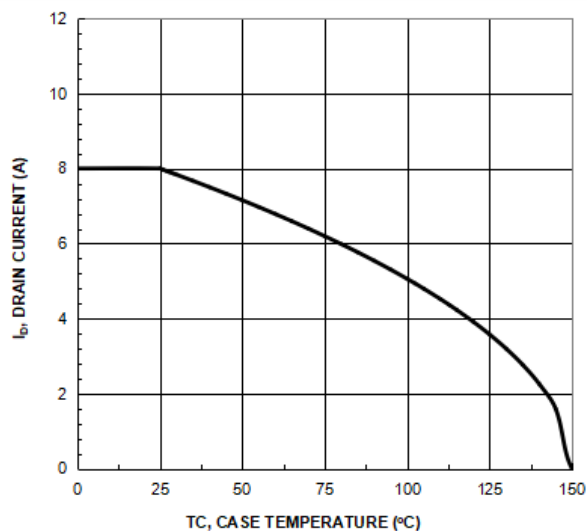
Power Dissipation

$$P_{tot}=f(T_C)$$



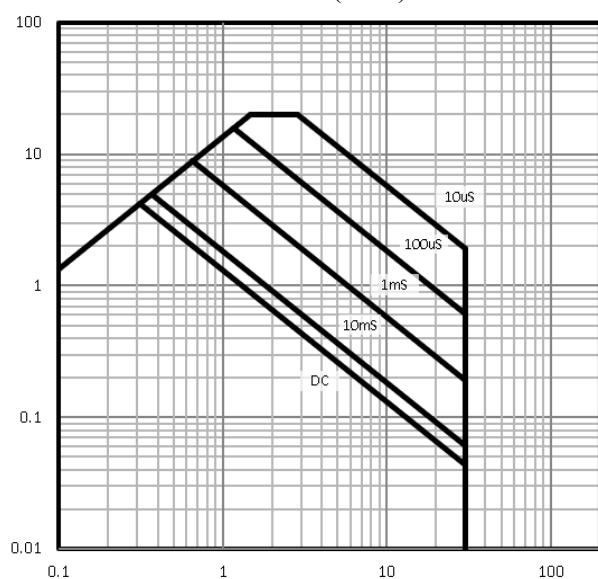
Maximum Drain Current

$$-I_D=f(T_C)$$



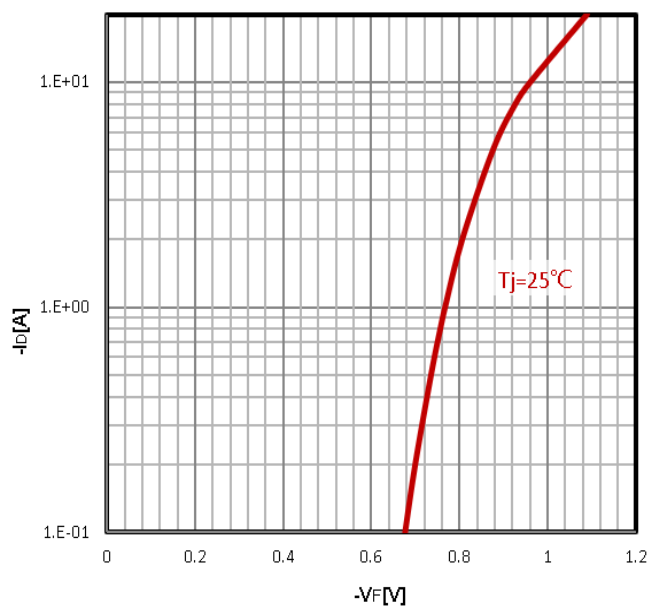
Safe operating area

$$-I_D=f(-V_{DS})$$



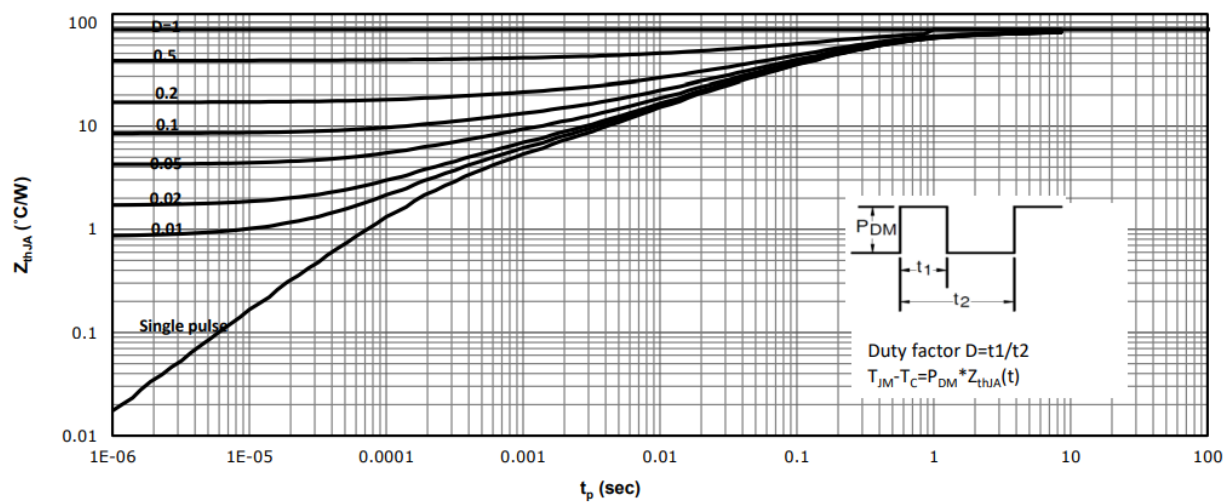
Body Diode Forward Voltage Variation

$$-I_F=f(-V_{DS})$$

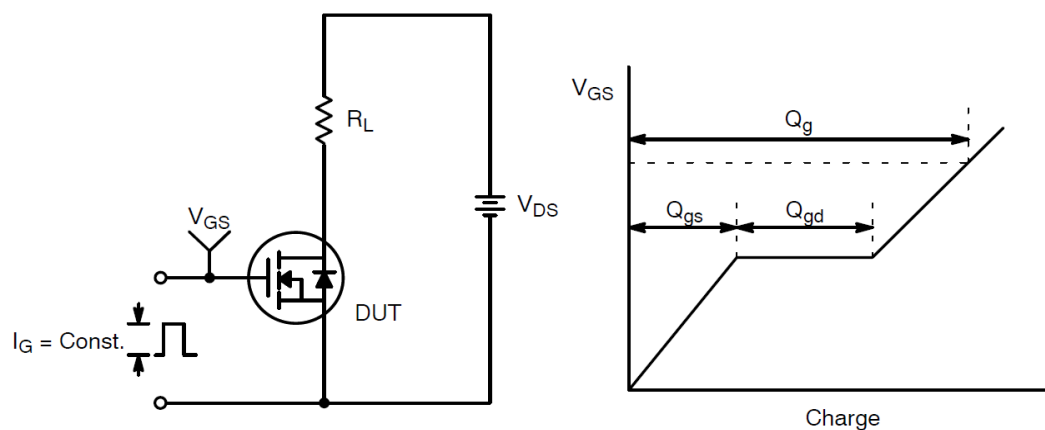


Max. transient thermal impedance

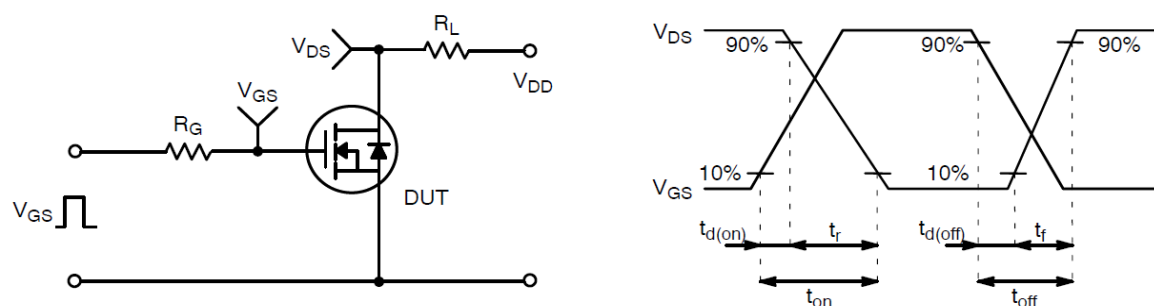
$$Z_{thJC}=f(t_p)$$



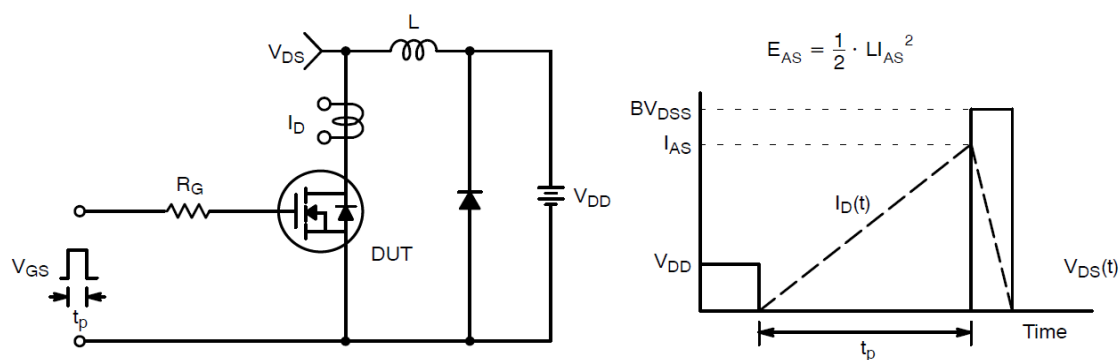
Test Circuit and Waveform:



Gate Charge Test Circuit & Waveform

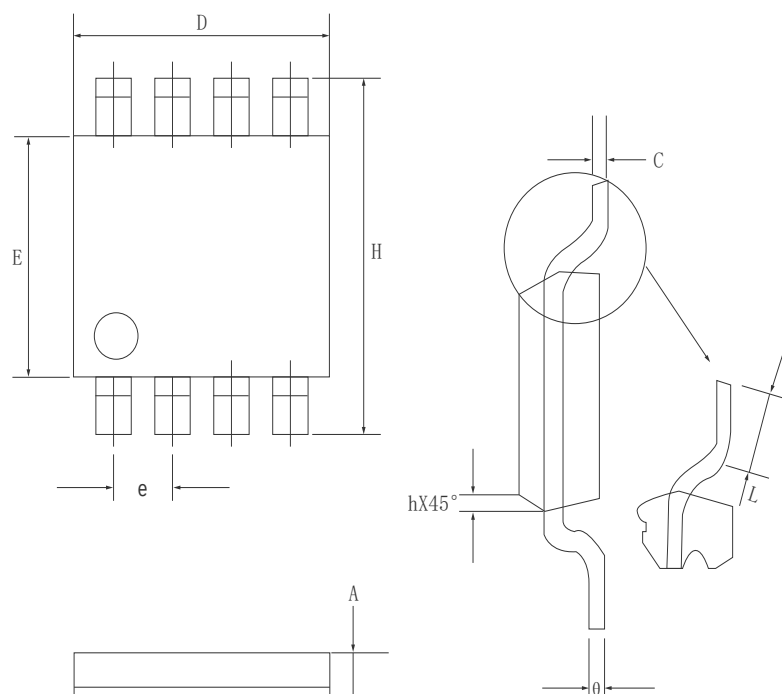


Resistive Switching Test Circuit & Waveforms

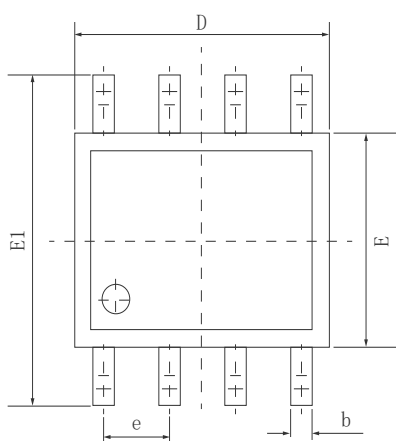
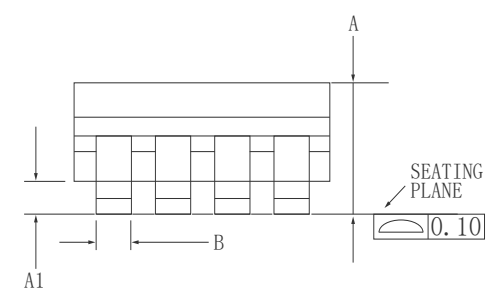


Unclamped Inductive Switching Test Circuit & Waveforms

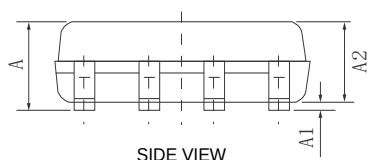
Dimensions (SOP8)



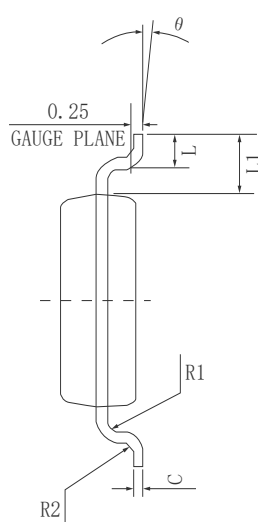
DIM	MILLIMETERS	
	MIN	MAX
A	1.35	1.75
A1	0.02	0.15
B	0.33	0.5
C	0.1	0.25
D	4.8	5
E	3.8	4
e	1.27 (BSC)	
H	5.8	6.2
h	0.25	0.5
I	0.4	1.25
θ	0°	7°



TOP VIEW



SIDE VIEW

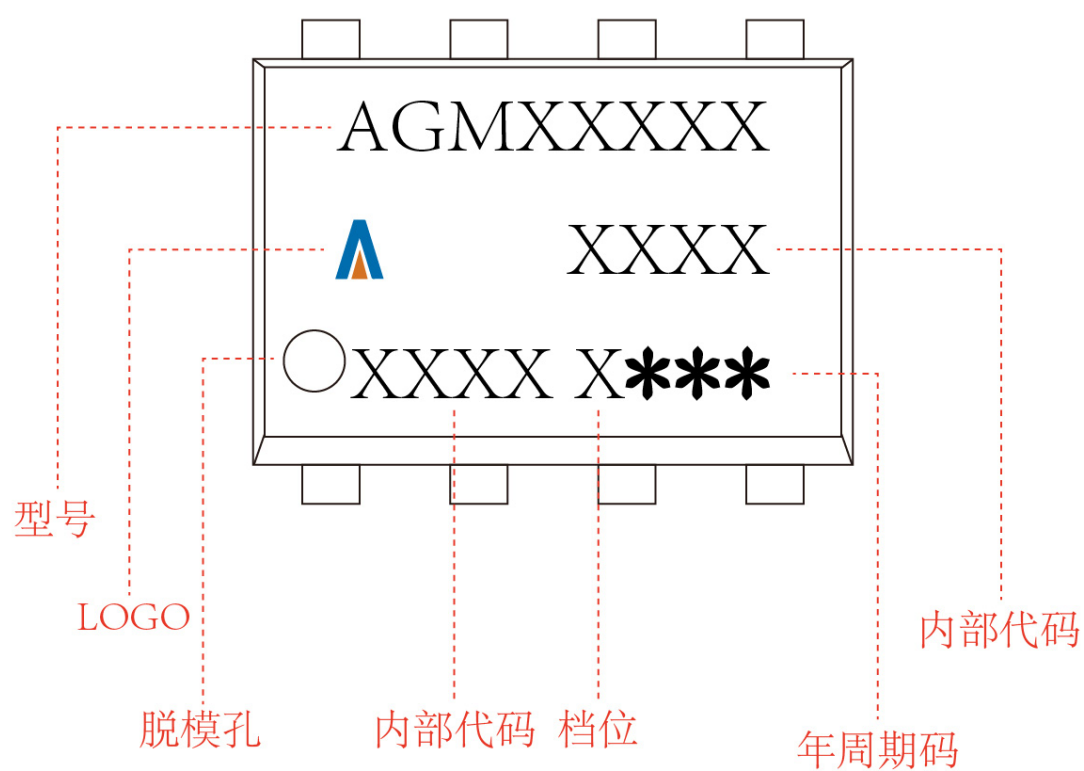


SIDE VIEW

SYMBOL	MIN	NOM	MAX
A	1.40	1.60	1.80
A1	0.05	0.15	0.25
A2	1.35	1.45	1.55
b	0.30	0.40	0.50
c	0.153	0.203	0.253
D	4.80	4.90	5.00
E	3.80	3.90	4.00
E1	5.80	6.00	6.20
L	0.45	0.70	1.00
θ	2°	4°	6°
L1	1.04 REF		
e	1.27 BSC		
R1	0.07 TYP		
R2	0.07 TYP		

SOP8

Marking Instructions:



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